TOSHIBA PHOTOCOUPLER GaAIAs IRED & PHOTO-IC

# TLP250(INV)

TRANSISTOR INVERTER
INVERTERS FOR AIR CONDITIONER
IGBT GATE DRIVE
POWER MOS FET GATE DRIVE

The TOSHIBA TLP250(INV) consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP.

TLP250(INV) is suitable for gate driving circuit of IGBT or power MOS FET.

Input Threshold Current : I<sub>F</sub>=5mA(MAX)
 Supply Current(ICC) : 11mA(MAX)
 Supply Voltage(VCC) : 10~35V
 Output Current(IO) : ±2.0A(MAX)
 Switching Time(tpLH/tpHL) : 0.5µs(MAX)
 Isolation Voltage : 2500Vrms

UL Recognized : UL1577,File No.E67349

Option(D4)

VDE Approved: DIN VDE0884/06.92 Certificate No.76823

Maximum Operating Insulation Voltage :  $630V_{PK}$ Highest Permissible Over Voltage :  $4000V_{PK}$ 

(Note):When a VDE0884 approved type is needed, Please designate the "Option(D4)"

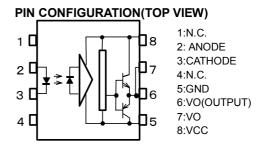
Creepage Distance : 6.4mm(MIN)
Clearance : 6.4mm(MIN)

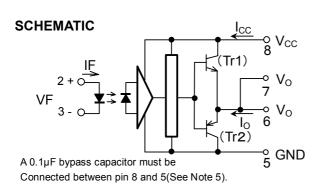
# Unit in mm 8 7 6 5 9.66 ± 0.25 1.2 ± 0.15 0.5 ± 0.1 2.54 ± 0.25 11-10C4 TOSHIBA 11-10C4

Weight: 0.54 g

### **TRUTH TABLE**

	Tr 1	Tr 2	
INPUT LED	ON	ON	OFF
IN OT LED	OFF	OFF	ON







## **MAXIMUM RATINGS (Ta=25°C)**

	CHARA	SYMBOL	RATING	UNIT			
Forward Current					20	mA	
	Forward Current Derating (Ta≥	ΔI <sub>F</sub> /ΔTa	-0.36	mA /°C			
LED	Peak Transient Forward Currer	(Note 1)	I <sub>FPT</sub>	1	Α		
	Reverse Voltage			$V_R$	5	V	
	Junction Temperature			Tj	125	°C	
	"H" Peak	PW ≤2.5µs , f≤15 kH:	2		-1.5	Α	
	Output Current	PW≤1.0µs , f≤15 kHz		I <sub>OPH</sub>	-2.0	A	
	"L" Peak	PW≤2.5µs , f≤15 kHz	(Note 2)		+1.5	^	
	Output Current	PW ≤1.0µs , f≤15 kH:	2	I <sub>OPL</sub>	+2.0	Α	
DETECTOR	Output Valtage		(Ta≤70°C)	Vo	35	V	
TEC	Output Voltage		(Ta=85°C)		24	V	
В	Supply Voltage		(Ta≤70°C)	V <sub>cc</sub>	35	V	
	Supply Vollage		(Ta=85°C)	V CC	24	V	
Output Voltage Derating (Ta≥70°C)				ΔV <sub>O</sub> /ΔTa	-0.73	V /°C	
	Supply Voltage Derating (Ta≥7	ΔV <sub>CC</sub> /ΔTa	-0.73	V /°C			
	Junction Temperature	T <sub>j</sub>	125	°C			
Оре	erating Frequency	f	25	kHz			
Оре	erating Temperature Range	T <sub>opr</sub>	-20~85	°C			
Stor	age Temperature Range	T <sub>stg</sub>	-55~125	°C			
Lea	d Soldering Temperature(10s)	T <sub>sol</sub>	260	°C			
Isola	ation Voltage (AC,1min., R.H. s	(Note 4)	BVs	2500	Vrms		

- (Note 1) : Pulse width PW≤1µs,300pps
- (Note 2): Exporenential Waveform
- (Note 3) : Exporenential Waveform  $I_{OPH} \le -1.0 A (\le 2.5 \mu s)$ ,  $I_{OPL} \le +1.0 A (\le 2.5 \mu s)$
- (Note 4): Device considerd a two terminal device: pins 1,2,3 and 4 shorted together and pins 5,6,7 and 8 shorted together.
- (Note 5): A ceramic capacitor(0.1μF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching proparty. The total lead length between capacitor and coupler should not exceed 1cm.

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### RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX		UNIT
Input Current, ON	I <sub>F (ON)</sub>	7	8	10		mA
Input Voltage, OFF	$V_{F(OFF)}$	0	1	0.8		V
Supply Voltage	V <sub>CC</sub>	15	_	30 20		V
Peak Output Current	I <sub>OPH</sub> / I <sub>OPL</sub>	_	_	±0.5		Α
Operating Temperature	T <sub>opr</sub>	-20	25	70	85	°C

# ELECTRICAL CHARACTERISTICS (Ta = -20~70°C,Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Input Forward Voltage		$V_{F}$	_	I <sub>F</sub> = 10 mA, Ta = 25°C		_	1.6	1.8	V		
Temperature Coefficient of Forward Voltage		ΔV <sub>F</sub> /ΔTa	_	I <sub>F</sub> = 10 mA			-2.0	1	mV /°C		
Input Reverse Current		$I_R$	_	V <sub>R</sub> = 5 V, Ta = 25°C		_	_	10	μΑ		
Input Capacitance		C <sub>T</sub>	_	V = 0, f = 1 MHz, Ta = 25°C			45	250	pF		
	"H" Level	I <sub>ОРН</sub>	2	V <sub>CC</sub> = 30 \	/	I <sub>F</sub> = 10 mA V <sub>8-6</sub> = 4 V	-1.0	-1.5	1	А	
Output Current	"L" Level	I <sub>OPL</sub>	1	(*1)		$I_F = 0$ $V_{6-5} = 2.5 \text{ V}$	1.0	2	ı	^	
Output Valtage	"H" Level	V <sub>OH</sub>	3	$V_{CC1}$ = +15 V $V_{EE1}$ = -15 V $R_L$ = 200 $\Omega$ , $I_F$ = 5 mA		11	12.8	-	· v		
Output Voltage	"L" Level	V <sub>OL</sub>	4	$V_{CC1} = +15 \text{ V}$ $V_{EE1} = -15 \text{ V}$ $R_L = 200\Omega, V_F = 0.8 \text{ V}$		_	-14.2	-12.5			
	"H" Level	Іссн	_	- V <sub>cc</sub> = 30 V		= 10 mA = 25°C	_	7	_	mA	
Supply Current					I <sub>F</sub> =	: 10 mA	-	_	11		
Зирріу Сипепі	"L" Level	I <sub>CCL</sub>			I <sub>F</sub> = 0 mA Ta = 25°C			1	7.5	ı	mA
					I <sub>F</sub> =	: 0 mA	1		11		
Threshold Input Current	L→H	I <sub>FLH</sub>		$V_{CC1} = +15 \text{ V}$ $V_{EE1} = -15 \text{ V}$ $R_L = 200\Omega, V_O > 0V$		_	1.2	5	mA		
Threshold Input Voltage	H→L	$V_{FHL}$	_	$V_{CC1} = +15 \text{ V}$ $V_{EE1} = -15 \text{ V}$ $R_L = 200\Omega, V_O < 0V$		0.8	_	_	٧		
Supply Voltage		V <sub>CC</sub>	_	_		10		35	V		
Capacitance (Input-Output)		Cs	_	V <sub>S</sub> = 0, f = 1 MHz, Ta = 25°C		1	1.0	2.0	pF		
Resistance (Input-Output)		Rs	_	V <sub>S</sub> = 500 V, Ta = 25°C R.H.≤60%		1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω		

(\*) : All typical values are at Ta=25°C

(\*1) : Duration of IO time ≤  $50\mu$ s

# **SWITCHING CHARACTERISTICS** (Ta = $-20\sim70^{\circ}$ C,Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Propagation	L→H	t <sub>pLH</sub>			0.05	0.15	0.5	
Delay Time	H→L	t <sub>pHL</sub>		I <sub>F</sub> = 8 mA,	0.05	0.15	0.5	
Switching Time Dispersion between ON and OFF Output Rise Time		tpHL-tpLH	5	$V_{CC} = 15 \text{ V}$		_	0.45	μs
				$R_1 = 20\Omega$ . $C_1 = 10$ nF				
		t <sub>r</sub>		N <sub>L</sub> = 2022, O <sub>L</sub> = 10111	_		_	
Output Fall Time		t <sub>f</sub>			_		_	
Common Mode Transient		CM <sub>H</sub>		V <sub>CM</sub> = 1000 V, I <sub>F</sub> = 8 mA	-15000			V /µs
Immunity at High Level Output			6	V <sub>CC</sub> = 30 V, Ta = 25°C	-15000	_	_	ν /μδ
Common Mode Transient		CML		V <sub>CM</sub> = 1000 V, I <sub>F</sub> = 0 mA	15000			V /µs
Immunity at Low Level Output				V <sub>CC</sub> = 30 V, Ta = 25°C	15000			ν /μδ

Fig.1 I<sub>OPL</sub> TEST CIRCUIT

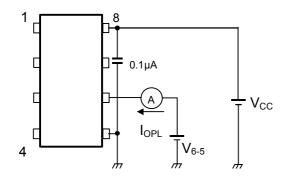


Fig.2 I<sub>OPH</sub> TEST CIRCUIT

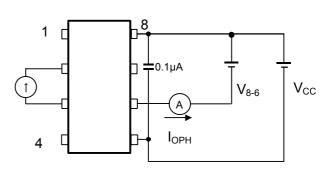


Fig.3 V<sub>OH</sub> TEST CIRCUIT

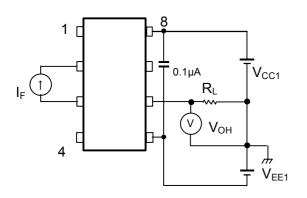


Fig.4 V<sub>OL</sub> TEST CIRCUIT

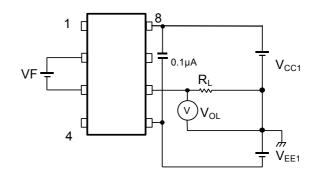
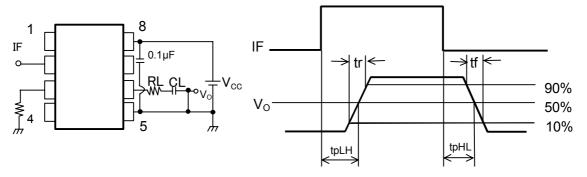


Fig.5 tpLH、tpHL、tr、tf TEST CIRCUIT

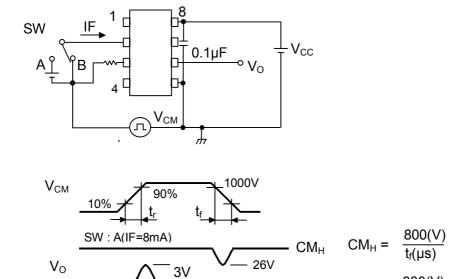


 $\mathsf{CM}_\mathsf{L}$ 

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Fig.6 CM<sub>H</sub>, CM<sub>L</sub> TEST CIRCUIT

SW: B(IF=0mA)



CML(CMH) is the maximum rate of rise(fall) of the common mode voltage that can be sustained with the output voltage in the low(high)state.

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000707EBC

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